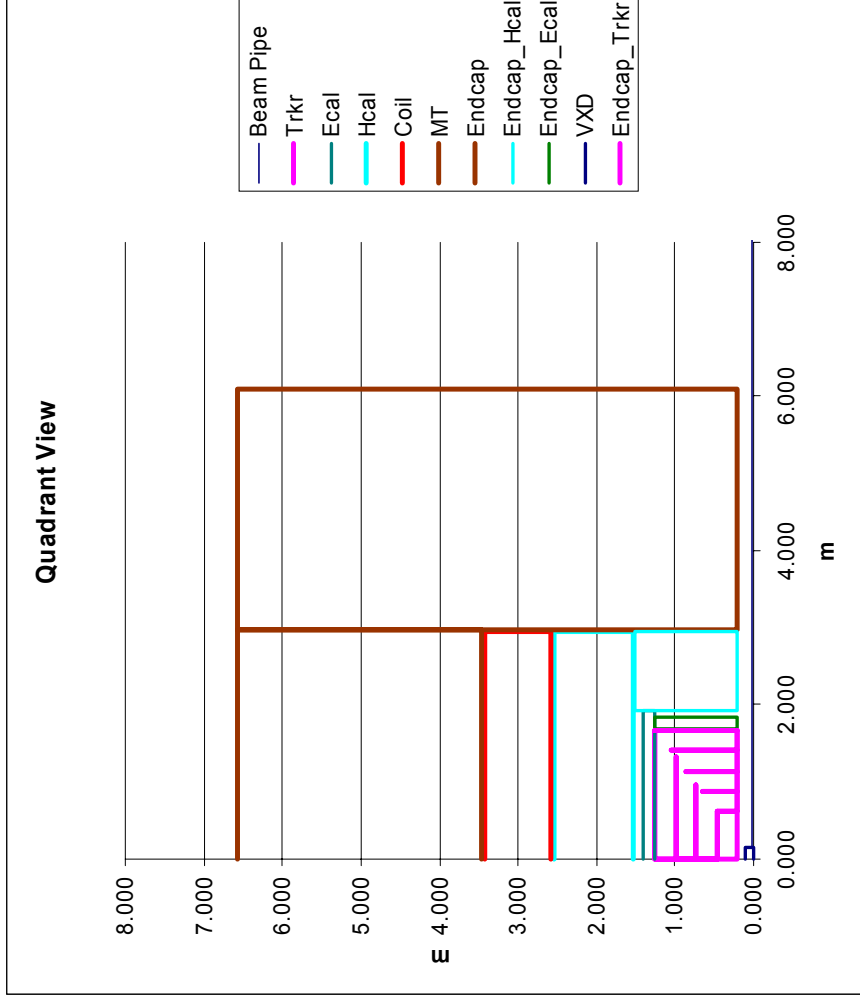


Design Considerations for a Si/W EM Cal. at a Linear Collider

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SD Detector

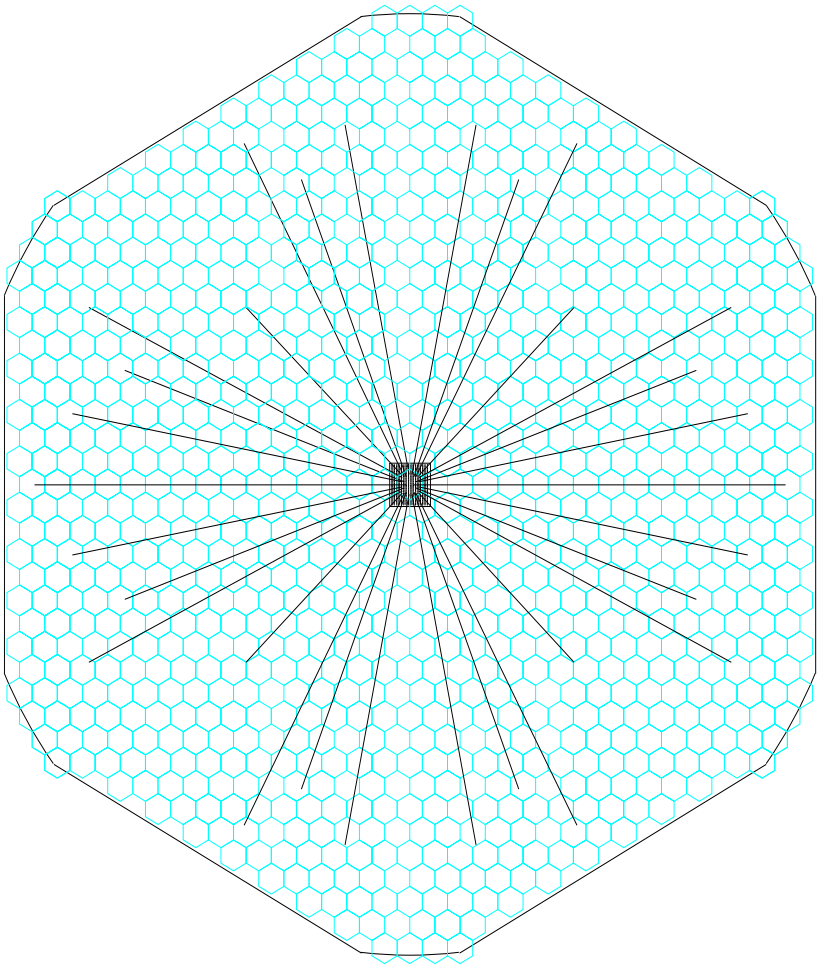
- SD designed for excellent energy flow performance – with well-understood and somewhat constrained cost
(see Snowmass Orange Book for details)
- Si/W ECal
 - 5mm transverse segmentation
 - [2.5 mm W (0.7 X₀), 0.4 mm Si] x30
 - R_m = 9mm (1 + gap(mm)/2.5) → Keep gaps small !

In this talk:

- Some architecture and readout issues
- Dynamic range and some electronics issues
- Next steps

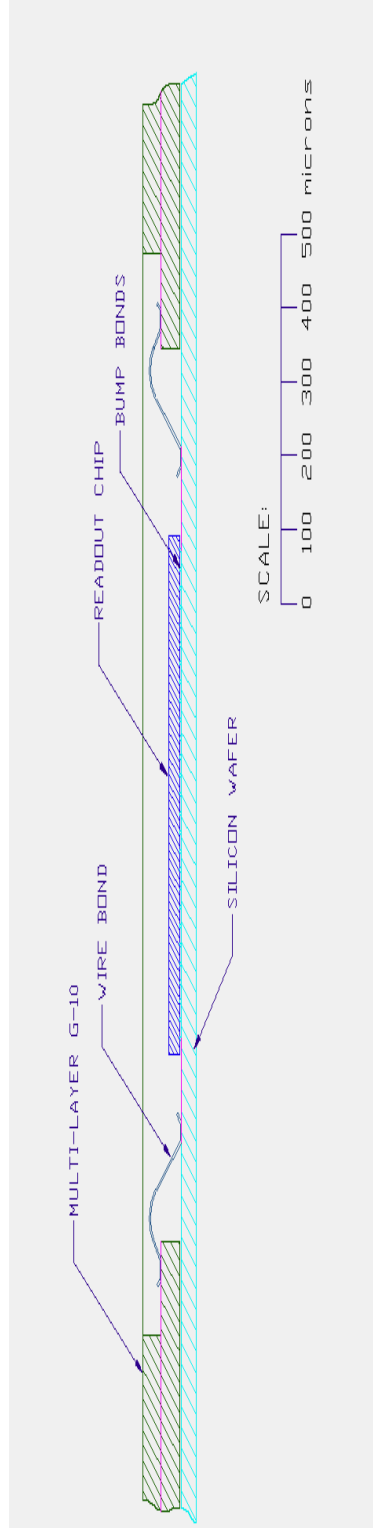
Si/W Readout-SD

- ~50 M pixels, 5x5 mm²
- Do NOT scale electronics by this number
- 1 chip per wafer
- 1 chip per ~1 m² of wafers



6 inch (152mm) WAFER

1,027 (5mm) CELLS



Noise

- GLAST Si electronics: $20\text{e/pF} + 200\text{e}$ → $\approx 2000\text{e}$ (fine)

Cooling

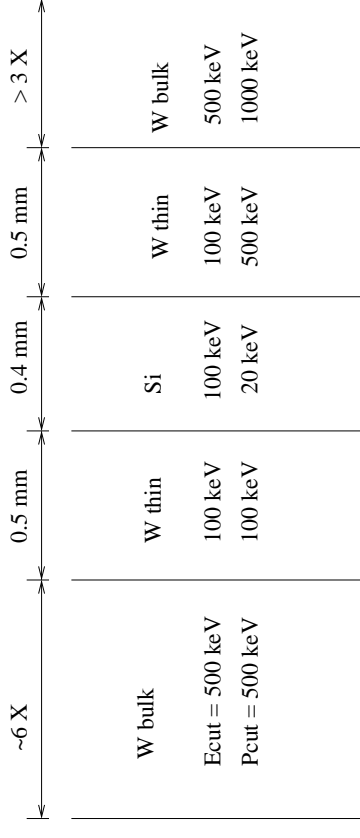
- NLC duty cycle is $\sim 10^{-4}$
 - Assume 10^{-3} power duty cycle
- GLAST elec. power: 2 mW/chan.
- For standard W alloy, can cool one edge of W plate
 - $\approx 2^\circ$ rise (fine)

Dynamic Range

- MIPs
- 500 GeV Bhabha electrons
- EGS study: ≈ 2000 MIPs
- Maintain low-end resolution
 - 3 ranges of 12 bits

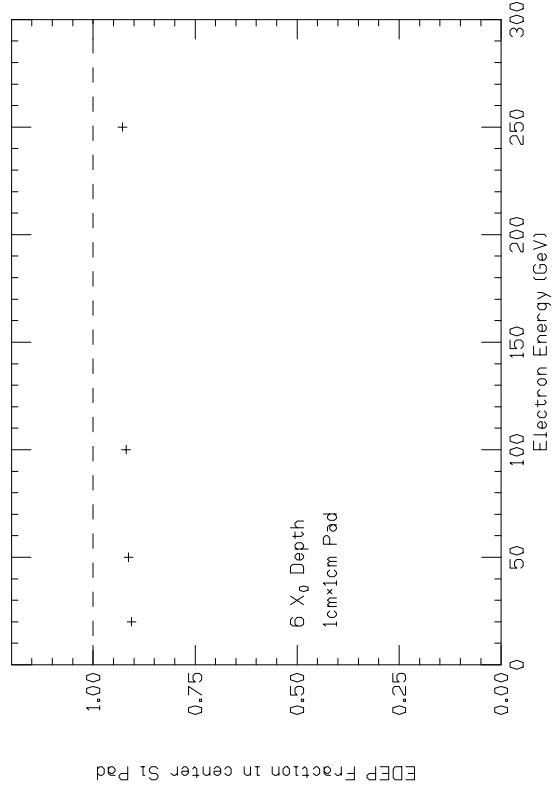
EGS Setup

- Use the G. Lindstrom, et al., recommendations* for E_{cut} in thin sampling layers. (Good accuracy with finite CPU time.)
- Reduced E_{cut} , P_{cut} in thin regions near the Si
- Step size small (0.3%) everywhere

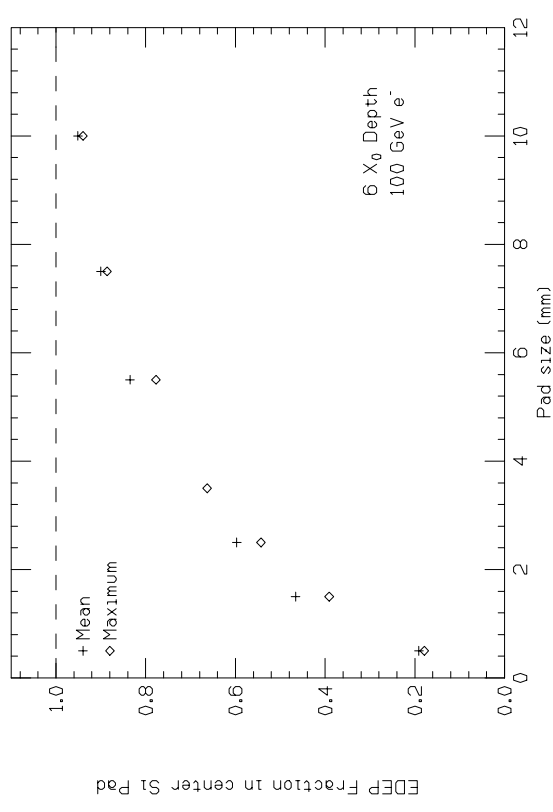


*Proc. Workshop on Calorimetry for the Supercollider (1989) 215-225.

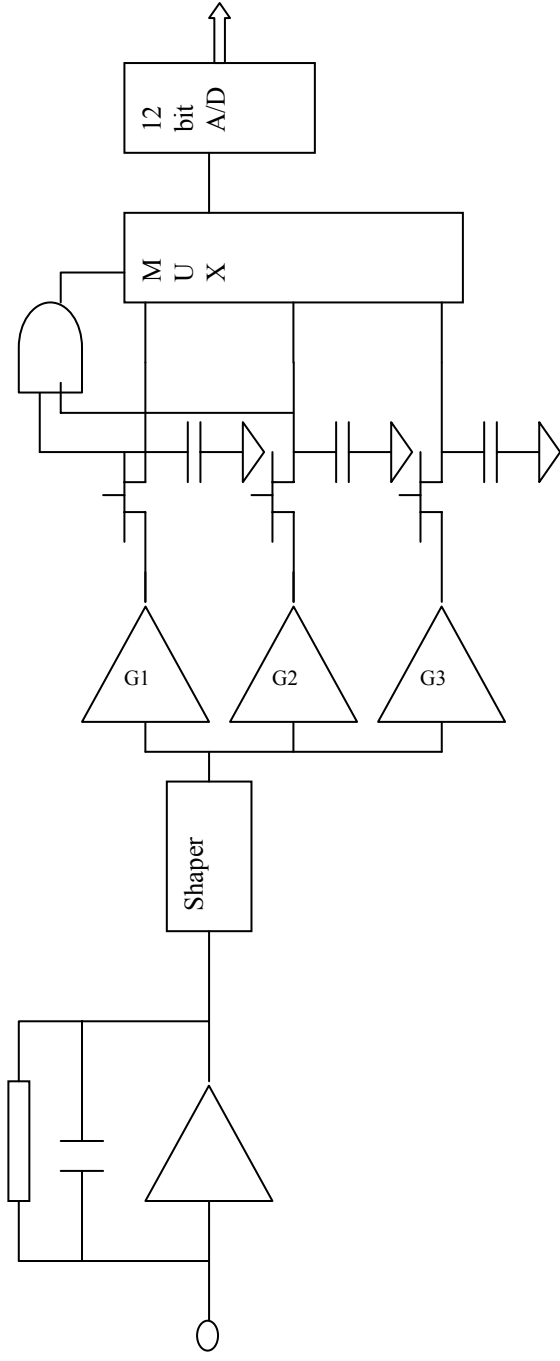
- Broad shower max in depth $\sim 6.5 \pm 1 X_0$
- Fraction of energy in central $1\text{cm} \times 1\text{cm}$ is \sim independent of E_e :



- EDEP fraction in center pixel as function of pixel size (mm):



\Rightarrow need big pixel size reduction to change dynamic range requirement significantly



- Charge amp. with ~ 10pf feedback cap.
- 3 ranges @ 12 bits

Next...

- Further design work
- Prototypes:
 - Silicon wafer with 5mm pixels and metallizations for wafer readout chip
 - Wafer readout chip
- The other readout chips
- A one wafer wide, full depth module for test beam